

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-Spice, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-Spice Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



| R-C VALUES FOR TANK CONFIGURATION | | | |
|--|---------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | N/A | 141.7251 m | N/A |
| RT2 | N/A | 88.3714 m | N/A |
| RT3 | N/A | 231.1810 m | N/A |
| RT4 | N/A | 38.7225 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | N/A | 111.9545 m | N/A |
| CT2 | N/A | 46.4999 m | N/A |
| CT3 | N/A | 264.1647 m | N/A |
| CT4 | N/A | 10.8135 m | N/A |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.



R-C THERMAL MODEL FOR FILTER CONFIGURATION



| R-C VALUES FOR FILTER CONFIGURATION | | | |
|--|---------|------------|------|
| Thermal Resistance ($^{\circ}\text{C}/\text{W}$) | | | |
| Junction to | Ambient | Case | Foot |
| RF1 | N/A | 80.7834 m | N/A |
| RF2 | N/A | 172.5803 m | N/A |
| RF3 | N/A | 135.1016 m | N/A |
| RF4 | N/A | 111.5347 m | N/A |
| Thermal Capacitance (Joules/ $^{\circ}\text{C}$) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | N/A | 8.5974 m | N/A |
| CF2 | N/A | 28.2127 m | N/A |
| CF3 | N/A | 78.2834 m | N/A |
| CF4 | N/A | 384.8007 m | N/A |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

